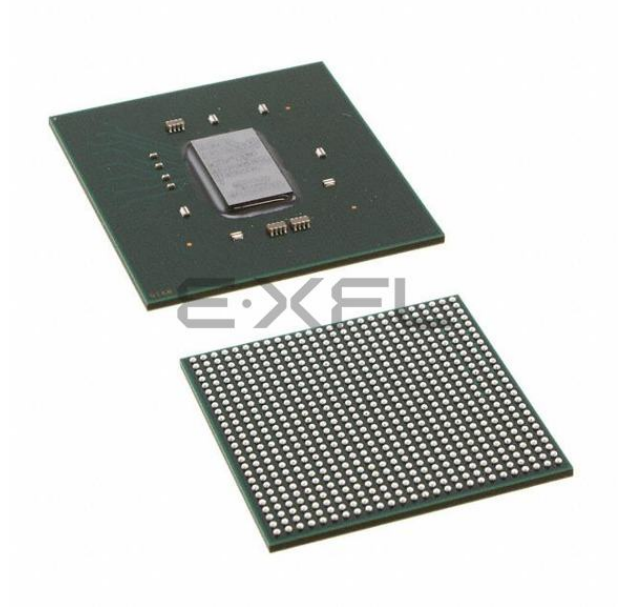

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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	5125
Number of Logic Elements/Cells	65600
Total RAM Bits	4976640
Number of I/O	300
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	676-BBGA, FCBGA
Supplier Device Package	676-FCBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k70t-1fbg676i

Table 1: **Absolute Maximum Ratings (1) *(Cont'd)***

Symbol	Description	Min	Max	Units
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (6)	–	+260	°C
T_j	Maximum junction temperature(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC and AC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions (1)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}(2)	Internal supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCBRAM}(2)	Block RAM supply voltage	0.97	1.00	1.03	V
	For -2L (0.9V) devices: block RAM supply voltage	0.87	0.90	1.03	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCO}(3)(4)	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
	Supply voltage for 1.8V HP I/O banks	1.14	–	1.89	V
V_{CCAUX_IO}	Auxiliary supply voltage when set to 1.8V	1.71	1.80	1.89	V
	Auxiliary supply voltage when set to 2.0V	1.94	2.00	2.06	V
V_{IN}(5)	I/O input voltage	–0.20	–	V_{CCO} + 0.2	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}(6)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(7)	Battery voltage	1.0	–	1.89	V
GTX Transceiver					
$V_{MGTAVCC}$(8)	Analog supply voltage for the GTX transceiver QPLL frequency range ≤ 10.3125 GHz(9)(10)	0.97	1.0	1.08	V
	Analog supply voltage for the GTX transceiver QPLL frequency range > 10.3125 GHz	1.02	1.05	1.08	V
$V_{MGTAVTT}$(8)	Analog supply voltage for the GTX transmitter and receiver termination circuits	1.17	1.2	1.23	V
$V_{MGTVCCAUX}$(8)	Auxiliary analog QPLL voltage supply for the transceivers	1.75	1.80	1.85	V

Table 2: **Recommended Operating Conditions (1) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$ (8)	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN} (2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT} (3)	Battery supply current	–	–	150	nA

Table 5: **Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks(1)(2) *(Cont'd)***

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.80	9.71	–0.80	50.0
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7K70T	241	241	241	187	mA
		XC7K160T	474	474	474	368	mA
		XC7K325T	810	810	810	629	mA
		XC7K355T	993	993	993	771	mA
		XC7K410T	1080	1080	1080	838	mA
		XC7K420T	1313	1313	1313	1019	mA
		XC7K480T	1313	1313	1313	1019	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7K70T	1	1	1	1	mA
		XC7K160T	1	1	1	1	mA
		XC7K325T	1	1	1	1	mA
		XC7K355T	1	1	1	1	mA
		XC7K410T	1	1	1	1	mA
		XC7K420T	1	1	1	1	mA
		XC7K480T	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7K70T	21	21	21	21	mA
		XC7K160T	40	40	40	40	mA
		XC7K325T	68	68	68	68	mA
		XC7K355T	75	75	75	75	mA
		XC7K410T	85	85	85	85	mA
		XC7K420T	99	99	99	99	mA
		XC7K480T	99	99	99	99	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7K70T	N/A	N/A	N/A	N/A	mA
		XC7K160T	2	2	2	2	mA
		XC7K325T	2	2	2	2	mA
		XC7K355T	N/A	N/A	N/A	N/A	mA
		XC7K410T	2	2	2	2	mA
		XC7K420T	N/A	N/A	N/A	N/A	mA
		XC7K480T	N/A	N/A	N/A	N/A	mA

Table 17: **Maximum Physical Interface (PHY) Rate for Memory Interfaces (FFG Packages)(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	2.0V	1866	1866	1600	1333	Mb/s
	HP	1.8V	1600	1333	1066	1066	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1600	1600	1333	1066	Mb/s
	HP	1.8V	1333	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	800	800	800	Mb/s
RLDRAM III(3)	HP	2.0V	800	667	667	533	MHz
	HP	1.8V	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	1066	1066	800	800	Mb/s
DDR3L	HP	2.0V	1066	1066	800	800	Mb/s
	HP	1.8V	1066	1066	800	800	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V					
	HR	N/A					
QDR II+(4)	HP	2.0V	550	500	450	450	MHz
	HP	1.8V					
	HR	N/A	500	450	400	400	MHz
RLDRAM II	HP	2.0V	533	500	450	450	MHz
	HP	1.8V					
	HR	N/A					
LPDDR2(3)	HP	2.0V	800	800	800	800	Mb/s
	HP	1.8V	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
4. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
HSTL_I_F	0.61	0.64	0.73	0.79	1.10	1.19	1.23	1.41	1.86	2.05	2.22	1.92	ns
HSTL_II_F	0.61	0.64	0.73	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
HSTL_I_18_F	0.64	0.67	0.76	0.79	1.05	1.18	1.28	1.44	1.81	2.04	2.27	1.95	ns
HSTL_II_18_F	0.64	0.67	0.76	0.79	1.03	1.14	1.23	1.42	1.79	2.00	2.22	1.94	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	0.78	1.09	1.18	1.22	1.48	1.85	2.04	2.21	2.00	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	0.79	1.02	1.11	1.14	1.48	1.78	1.97	2.13	2.00	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	0.79	1.08	1.17	1.21	1.48	1.84	2.03	2.20	2.00	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	0.81	1.01	1.10	1.13	1.48	1.77	1.96	2.12	2.00	ns
LVCMOS33_S4	1.31	1.40	1.60	1.54	5.23	5.61	6.09	4.13	5.99	6.47	7.08	4.64	ns
LVCMOS33_S8	1.31	1.40	1.60	1.54	4.46	4.85	5.33	3.84	5.22	5.71	6.32	4.36	ns
LVCMOS33_S12	1.31	1.40	1.60	1.54	3.46	3.89	4.42	3.41	4.22	4.75	5.41	3.92	ns
LVCMOS33_S16	1.31	1.40	1.60	1.54	3.06	3.43	3.88	3.72	3.82	4.29	4.87	4.23	ns
LVCMOS33_F4	1.31	1.40	1.60	1.54	4.70	5.01	5.36	3.58	5.46	5.87	6.35	4.09	ns
LVCMOS33_F8	1.31	1.40	1.60	1.54	3.62	4.04	4.56	3.06	4.38	4.90	5.55	3.58	ns
LVCMOS33_F12	1.31	1.40	1.60	1.54	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVCMOS33_F16	1.31	1.40	1.60	1.54	2.44	2.69	2.96	2.88	3.20	3.55	3.95	3.39	ns
LVCMOS25_S4	1.08	1.16	1.32	1.36	4.49	4.80	5.16	3.44	5.25	5.66	6.15	3.95	ns
LVCMOS25_S8	1.08	1.16	1.32	1.36	3.66	4.04	4.49	3.20	4.42	4.90	5.48	3.72	ns
LVCMOS25_S12	1.08	1.16	1.32	1.36	2.77	3.10	3.49	2.80	3.53	3.96	4.48	3.31	ns
LVCMOS25_S16	1.08	1.16	1.32	1.36	3.24	3.62	4.09	3.14	4.00	4.48	5.08	3.66	ns
LVCMOS25_F4	1.08	1.16	1.32	1.36	3.96	4.31	4.72	3.06	4.72	5.17	5.71	3.58	ns
LVCMOS25_F8	1.08	1.16	1.32	1.36	2.43	2.87	3.42	2.50	3.19	3.73	4.41	3.02	ns
LVCMOS25_F12	1.08	1.16	1.32	1.36	2.23	2.63	3.13	2.48	2.99	3.49	4.12	3.00	ns
LVCMOS25_F16	1.08	1.16	1.32	1.36	1.92	2.17	2.45	2.33	2.68	3.03	3.44	2.84	ns
LVCMOS18_S4	0.64	0.66	0.74	0.87	3.24	3.45	3.66	1.91	4.00	4.31	4.65	2.42	ns
LVCMOS18_S8	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S12	0.64	0.66	0.74	0.87	2.58	2.91	3.31	2.50	3.34	3.77	4.30	3.02	ns
LVCMOS18_S16	0.64	0.66	0.74	0.87	1.82	2.03	2.24	1.84	2.58	2.89	3.23	2.36	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	0.87	1.74	1.92	2.08	1.92	2.50	2.78	3.07	2.44	ns
LVCMOS18_F4	0.64	0.66	0.74	0.87	3.12	3.31	3.49	1.77	3.88	4.17	4.48	2.28	ns
LVCMOS18_F8	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F12	0.64	0.66	0.74	0.87	1.91	2.13	2.36	2.00	2.67	2.99	3.35	2.52	ns
LVCMOS18_F16	0.64	0.66	0.74	0.87	1.52	1.68	1.81	1.72	2.28	2.54	2.80	2.23	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	0.87	1.34	1.46	1.55	1.66	2.10	2.32	2.54	2.17	ns
LVCMOS15_S4	0.66	0.69	0.81	0.90	3.48	3.74	4.03	2.22	4.24	4.60	5.02	2.73	ns
LVCMOS15_S8	0.66	0.69	0.81	0.90	2.37	2.67	3.01	2.41	3.13	3.53	4.00	2.92	ns
LVCMOS15_S12	0.66	0.69	0.81	0.90	1.83	2.03	2.23	1.91	2.59	2.89	3.22	2.42	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVDS	0.75	0.79	0.92	0.89	1.05	1.17	1.24	1.43	1.68	1.92	2.06	2.04	ns
HSUL_12	0.69	0.72	0.82	0.95	1.65	1.84	2.05	1.80	2.29	2.59	2.87	2.41	ns
DIFF_HSUL_12	0.69	0.72	0.82	0.92	1.65	1.84	2.05	1.47	2.29	2.59	2.87	2.08	ns
HSTL_I_S	0.68	0.72	0.82	0.84	1.15	1.28	1.38	1.46	1.79	2.03	2.20	2.07	ns
HSTL_II_S	0.68	0.72	0.82	0.84	1.05	1.17	1.26	1.44	1.69	1.93	2.08	2.05	ns
HSTL_I_18_S	0.70	0.72	0.82	0.86	1.12	1.24	1.34	1.41	1.75	2.00	2.16	2.02	ns
HSTL_II_18_S	0.70	0.72	0.82	0.86	1.06	1.18	1.26	1.44	1.70	1.94	2.08	2.05	ns
HSTL_I_12_S	0.68	0.72	0.82	0.94	1.14	1.27	1.37	1.43	1.78	2.02	2.20	2.04	ns
HSTL_I_DCI_S	0.68	0.72	0.82	0.78	1.11	1.23	1.33	1.36	1.74	1.99	2.15	1.98	ns
HSTL_II_DCI_S	0.68	0.72	0.82	0.78	1.05	1.17	1.26	1.33	1.69	1.93	2.08	1.94	ns
HSTL_II_T_DCI_S	0.70	0.72	0.82	0.76	1.15	1.28	1.38	1.40	1.78	2.03	2.20	2.01	ns
HSTL_I_DCI_18_S	0.70	0.72	0.82	0.76	1.11	1.23	1.33	1.36	1.74	1.99	2.15	1.98	ns
HSTL_II_DCI_18_S	0.70	0.72	0.82	0.76	1.05	1.16	1.24	1.32	1.69	1.92	2.06	1.93	ns
HSTL_II _T_DCI_18_S	0.70	0.72	0.82	0.76	1.11	1.23	1.33	1.36	1.74	1.99	2.15	1.98	ns
DIFF_HSTL_I_S	0.75	0.79	0.92	0.89	1.15	1.28	1.38	1.47	1.79	2.03	2.20	2.08	ns
DIFF_HSTL_II_S	0.75	0.79	0.92	0.89	1.05	1.17	1.26	1.47	1.69	1.93	2.08	2.08	ns
DIFF_HSTL_I_DCI_S	0.75	0.79	0.92	0.76	1.15	1.28	1.38	1.47	1.78	2.03	2.20	2.08	ns
DIFF_HSTL_II_DCI_S	0.75	0.79	0.92	0.76	1.05	1.17	1.26	1.40	1.69	1.93	2.08	2.01	ns
DIFF_HSTL_I_18_S	0.75	0.79	0.92	0.89	1.12	1.24	1.34	1.46	1.75	2.00	2.16	2.07	ns
DIFF_HSTL_II_18_S	0.75	0.79	0.92	0.89	1.06	1.18	1.26	1.47	1.70	1.94	2.08	2.08	ns
DIFF_HSTL_I_DCI_18_S	0.75	0.79	0.92	0.75	1.11	1.23	1.33	1.46	1.74	1.99	2.15	2.07	ns
DIFF_HSTL_II_DCI_18_S	0.75	0.79	0.92	0.75	1.05	1.16	1.24	1.41	1.69	1.92	2.06	2.02	ns
DIFF_HSTL_II _T_DCI_18_S	0.75	0.79	0.92	0.76	1.11	1.23	1.33	1.46	1.74	1.99	2.15	2.07	ns
HSTL_I_F	0.68	0.72	0.82	0.84	1.02	1.14	1.22	1.26	1.66	1.90	2.04	1.87	ns
HSTL_II_F	0.68	0.72	0.82	0.84	0.97	1.08	1.15	1.29	1.61	1.84	1.97	1.90	ns
HSTL_I_18_F	0.70	0.72	0.82	0.86	1.04	1.16	1.24	1.32	1.68	1.91	2.06	1.93	ns
HSTL_II_18_F	0.70	0.72	0.82	0.86	0.98	1.09	1.16	1.35	1.62	1.85	1.98	1.96	ns
HSTL_I_12_F	0.68	0.72	0.82	0.94	1.02	1.13	1.21	1.26	1.65	1.88	2.03	1.87	ns
HSTL_I_DCI_F	0.68	0.72	0.82	0.78	1.04	1.16	1.24	1.30	1.67	1.91	2.06	1.91	ns
HSTL_II_DCI_F	0.68	0.72	0.82	0.78	0.97	1.08	1.15	1.22	1.61	1.84	1.97	1.83	ns
HSTL_II_T_DCI_F	0.70	0.72	0.82	0.76	1.02	1.14	1.22	1.26	1.66	1.90	2.04	1.87	ns
HSTL_I_DCI_18_F	0.70	0.72	0.82	0.76	1.04	1.16	1.24	1.30	1.67	1.91	2.06	1.91	ns
HSTL_II_DCI_18_F	0.70	0.72	0.82	0.76	0.98	1.09	1.16	1.27	1.61	1.85	1.98	1.88	ns
HSTL_II _T_DCI_18_F	0.70	0.72	0.82	0.76	1.04	1.16	1.24	1.30	1.67	1.91	2.06	1.91	ns
DIFF_HSTL_I_F	0.75	0.79	0.92	0.89	1.02	1.14	1.22	1.35	1.66	1.90	2.04	1.96	ns
DIFF_HSTL_II_F	0.75	0.79	0.92	0.89	0.97	1.08	1.15	1.35	1.61	1.84	1.97	1.96	ns
DIFF_HSTL_I_DCI_F	0.75	0.79	0.92	0.76	1.02	1.14	1.22	1.35	1.66	1.90	2.04	1.96	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
DIFF_HSTL_II_DCI_F	0.75	0.79	0.92	0.76	0.97	1.08	1.15	1.30	1.61	1.84	1.97	1.91	ns
DIFF_HSTL_I_18_F	0.75	0.79	0.92	0.89	1.04	1.16	1.24	1.38	1.68	1.91	2.06	1.99	ns
DIFF_HSTL_II_18_F	0.75	0.79	0.92	0.89	0.98	1.09	1.16	1.40	1.62	1.85	1.98	2.01	ns
DIFF_HSTL_I_DCI_18_F	0.75	0.79	0.92	0.75	1.04	1.16	1.24	1.38	1.67	1.91	2.06	1.99	ns
DIFF_HSTL_II_DCI_18_F	0.75	0.79	0.92	0.75	0.98	1.09	1.16	1.33	1.61	1.85	1.98	1.94	ns
DIFF_HSTL_II _T_DCI_18_F	0.75	0.79	0.92	0.76	1.04	1.16	1.24	1.38	1.67	1.91	2.06	1.99	ns
LVCMOS18_S2	0.47	0.50	0.60	0.87	3.95	4.28	4.85	3.40	4.59	5.04	5.67	4.01	ns
LVCMOS18_S4	0.47	0.50	0.60	0.87	2.67	2.98	3.43	2.69	3.31	3.73	4.26	3.30	ns
LVCMOS18_S6	0.47	0.50	0.60	0.87	2.14	2.38	2.72	2.18	2.77	3.14	3.54	2.79	ns
LVCMOS18_S8	0.47	0.50	0.60	0.87	1.98	2.21	2.52	2.02	2.61	2.97	3.35	2.63	ns
LVCMOS18_S12	0.47	0.50	0.60	0.87	1.70	1.91	2.17	1.85	2.34	2.67	2.99	2.46	ns
LVCMOS18_S16	0.47	0.50	0.60	0.87	1.57	1.75	1.97	1.76	2.20	2.51	2.79	2.37	ns
LVCMOS18_F2	0.47	0.50	0.60	0.87	3.50	3.87	4.48	2.85	4.14	4.63	5.30	3.46	ns
LVCMOS18_F4	0.47	0.50	0.60	0.87	2.23	2.50	2.87	2.26	2.87	3.25	3.69	2.87	ns
LVCMOS18_F6	0.47	0.50	0.60	0.87	1.80	2.00	2.26	1.52	2.43	2.76	3.08	2.13	ns
LVCMOS18_F8	0.47	0.50	0.60	0.87	1.46	1.72	2.04	1.51	2.10	2.47	2.86	2.12	ns
LVCMOS18_F12	0.47	0.50	0.60	0.87	1.26	1.40	1.53	1.46	1.89	2.16	2.35	2.07	ns
LVCMOS18_F16	0.47	0.50	0.60	0.87	1.19	1.33	1.44	1.46	1.83	2.08	2.26	2.07	ns
LVCMOS15_S2	0.59	0.62	0.73	0.86	3.55	3.89	4.45	3.11	4.19	4.65	5.27	3.73	ns
LVCMOS15_S4	0.59	0.62	0.73	0.86	2.45	2.70	3.06	2.46	3.08	3.45	3.89	3.07	ns
LVCMOS15_S6	0.59	0.62	0.73	0.86	2.24	2.51	2.88	2.33	2.88	3.26	3.71	2.94	ns
LVCMOS15_S8	0.59	0.62	0.73	0.86	1.91	2.16	2.49	2.05	2.55	2.91	3.31	2.66	ns
LVCMOS15_S12	0.59	0.62	0.73	0.86	1.77	1.98	2.23	1.97	2.41	2.73	3.05	2.58	ns
LVCMOS15_S16	0.59	0.62	0.73	0.86	1.62	1.81	2.02	1.85	2.26	2.56	2.84	2.46	ns
LVCMOS15_F2	0.59	0.62	0.73	0.86	3.38	3.69	4.18	2.74	4.02	4.44	5.00	3.35	ns
LVCMOS15_F4	0.59	0.62	0.73	0.86	2.04	2.21	2.44	1.72	2.68	2.97	3.26	2.33	ns
LVCMOS15_F6	0.59	0.62	0.73	0.86	1.47	1.74	2.09	1.49	2.10	2.50	2.91	2.10	ns
LVCMOS15_F8	0.59	0.62	0.73	0.86	1.31	1.46	1.61	1.47	1.95	2.22	2.43	2.08	ns
LVCMOS15_F12	0.59	0.62	0.73	0.86	1.21	1.34	1.45	1.44	1.84	2.10	2.27	2.05	ns
LVCMOS15_F16	0.59	0.62	0.73	0.86	1.18	1.31	1.41	1.41	1.82	2.07	2.23	2.02	ns
LVCMOS12_S2	0.64	0.67	0.78	0.95	3.38	3.80	4.48	3.27	4.02	4.55	5.30	3.88	ns
LVCMOS12_S4	0.64	0.67	0.78	0.95	2.62	2.94	3.43	2.76	3.26	3.70	4.25	3.37	ns
LVCMOS12_S6	0.64	0.67	0.78	0.95	2.05	2.33	2.72	2.24	2.69	3.08	3.54	2.85	ns
LVCMOS12_S8	0.64	0.67	0.78	0.95	1.94	2.18	2.51	2.16	2.58	2.94	3.33	2.77	ns
LVCMOS12_F2	0.64	0.67	0.78	0.95	2.84	3.15	3.62	2.47	3.48	3.90	4.44	3.08	ns
LVCMOS12_F4	0.64	0.67	0.78	0.95	1.97	2.18	2.44	1.69	2.61	2.93	3.26	2.30	ns
LVCMOS12_F6	0.64	0.67	0.78	0.95	1.33	1.51	1.70	1.43	1.96	2.26	2.52	2.04	ns

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Input/Output Logic Switching Characteristics

Table 22: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{ICE1CK}/T_{ICKCE1}	CE1 pin Setup/Hold with respect to CLK	0.42/0.00	0.48/0.00	0.67/0.00	0.56/–0.16	ns
T_{ISRCK}/T_{ICKSR}	SR pin Setup/Hold with respect to CLK	0.53/0.01	0.61/0.01	0.99/0.01	0.88/–0.30	ns
$T_{IDOCKE2}/T_{IOCKDE2}$	D pin Setup/Hold with respect to CLK without Delay (HP I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	0.01/0.41	ns
$T_{IDOCKDE2}/T_{IOCKDDE2}$	DDLY pin Setup/Hold with respect to CLK (using IDELAY) (HP I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	0.01/0.41	ns
$T_{IDOCKE3}/T_{IOCKDE3}$	D pin Setup/Hold with respect to CLK without Delay (HR I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	0.01/0.41	ns
$T_{IDOCKDE3}/T_{IOCKDDE3}$	DDLY pin Setup/Hold with respect to CLK (using IDELAY) (HR I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	0.01/0.41	ns
Combinatorial						
T_{IDIE2}	D pin to O pin propagation delay, no Delay (HP I/O banks only)	0.09	0.10	0.12	0.14	ns
T_{IDIDE2}	DDLY pin to O pin propagation delay (using IDELAY) (HP I/O banks only)	0.10	0.11	0.13	0.15	ns
T_{IDIE3}	D pin to O pin propagation delay, no Delay (HR I/O banks only)	0.09	0.10	0.12	0.14	ns
T_{IDIDE3}	DDLY pin to O pin propagation delay (using IDELAY) (HR I/O banks only)	0.10	0.11	0.13	0.15	ns
Sequential Delays						
T_{IDLOE2}	D pin to Q1 pin using flip-flop as a latch without Delay (HP I/O banks only)	0.36	0.39	0.45	0.54	ns
$T_{IDLODE2}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HP I/O banks only)	0.36	0.39	0.45	0.55	ns
T_{IDLOE3}	D pin to Q1 pin using flip-flop as a latch without Delay (HR I/O banks only)	0.36	0.39	0.45	0.54	ns
$T_{IDLODE3}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HR I/O banks only)	0.36	0.39	0.45	0.55	ns
T_{ICKQ}	CLK to Q outputs	0.47	0.50	0.58	0.71	ns
$T_{RQ\_ILOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.84	0.94	1.16	1.32	ns
$T_{GSRQ\_ILOGICE2}$	Global Set/Reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	11.39	ns
$T_{RQ\_ILOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.84	0.94	1.16	1.32	ns
$T_{GSRQ\_ILOGICE3}$	Global Set/Reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	11.39	ns
Set/Reset						
$T_{RPW\_ILOGICE2}$	Minimum Pulse Width, SR inputs (HP I/O banks only)	0.54	0.63	0.63	0.68	ns, Min
$T_{RPW\_ILOGICE3}$	Minimum Pulse Width, SR inputs (HR I/O banks only)	0.54	0.63	0.63	0.68	ns, Min

Table 23: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{ODCK}/T_{OCKD}	D1/D2 pins Setup/Hold with respect to CLK	0.45/–0.13	0.50/–0.13	0.58/–0.13	0.79/–0.18	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin Setup/Hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	0.35/–0.10	ns
T_{OSRCK}/T_{OCKSR}	SR pin Setup/Hold with respect to CLK	0.32/0.18	0.38/0.18	0.70/0.18	0.62/–0.04	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins Setup/Hold with respect to CLK	0.49/–0.16	0.56/–0.16	0.68/–0.16	0.67/–0.18	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin Setup/Hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	0.31/–0.10	ns
Combinatorial						
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.73	0.81	0.97	1.18	ns
Sequential Delays						
T_{OCKQ}	CLK to OQ/TQ out	0.41	0.43	0.49	0.63	ns
$T_{RQ\_OLOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.63	0.70	0.83	1.12	ns
$T_{GSRQ\_OLOGICE2}$	Global Set/Reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	11.39	ns
$T_{RQ\_OLOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.63	0.70	0.83	1.12	ns
$T_{GSRQ\_OLOGICE3}$	Global Set/Reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	11.39	ns
Set/Reset						
$T_{RPW\_OLOGICE2}$	Minimum Pulse Width, SR inputs (HP I/O banks only)	0.54	0.54	0.63	0.68	ns, Min
$T_{RPW\_OLOGICE3}$	Minimum Pulse Width, SR inputs (HR I/O banks only)	0.54	0.54	0.63	0.68	ns, Min

Output Serializer/Deserializer Switching Characteristics

Table 25: **OSERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{OSDCK_D}/T_{OSCKD_D}	D input Setup/Hold with respect to CLKDIV	0.37/0.02	0.40/0.02	0.55/0.02	0.44/–0.24	ns
T_{OSDCK_T}/T_{OSCKD_T}(1)	T input Setup/Hold with respect to CLK	0.49/–0.15	0.56/–0.15	0.68/–0.15	0.67/–0.25	ns
$T_{OSDCK\_T2}/T_{OSCKD\_T2}$(1)	T input Setup/Hold with respect to CLKDIV	0.27/–0.15	0.30/–0.15	0.34/–0.15	0.46/–0.25	ns
$T_{OSCCK\_OCE}/T_{OSCKC\_OCE}$	OCE input Setup/Hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	0.35/–0.15	ns
T_{OSCCK_S}	SR (Reset) input Setup with respect to CLKDIV	0.41	0.46	0.75	0.70	ns
$T_{OSCCK\_TCE}/T_{OSCKC\_TCE}$	TCE input Setup/Hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	0.31/–0.15	ns
Sequential Delays						
T_{OSCKO_OQ}	Clock to out from CLK to OQ	0.35	0.37	0.42	0.54	ns
T_{OSCKO_TQ}	Clock to out from CLK to TQ	0.41	0.43	0.49	0.63	ns
Combinatorial						
T_{OSDO_TTQ}	T input to TQ Out	0.73	0.81	0.97	1.18	ns

Notes:

1. T_{OSDCK_T2} and T_{OSCKD_T2} are reported as T_{OSDCK_T}/T_{OSCKD_T} in TRACE report.

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 29: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{SHCKO}	Clock to A – B outputs	0.68	0.70	0.85	1.08	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	0.91	0.95	1.15	1.44	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK	0.45/0.23	0.45/0.24	0.54/0.27	0.69/0.33	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock	0.13/0.50	0.14/0.50	0.17/0.58	0.21/0.63	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.40/0.16	0.42/0.17	0.52/0.23	0.63/0.23	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock	0.29/0.09	0.30/0.09	0.36/0.09	0.46/0.10	ns, Min
T_{CECK_LRAM}/ T_{CKCE_LRAM}	CE input to CLK	0.29/0.09	0.30/0.09	0.37/0.09	0.47/0.10	ns, Min
Clock CLK						
T_{MPW}	Minimum pulse width	0.68	0.77	0.91	1.11	ns, Min
T_{MCP}	Minimum clock period	1.35	1.54	1.82	2.22	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 30: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	0.96	0.98	1.20	1.35	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.19	1.23	1.50	1.72	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	0.89	0.91	1.10	1.25	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{WS_SHFREG}/ T_{WH_SHFREG}	WE input	0.26/0.09	0.27/0.09	0.33/0.09	0.41/0.10	ns, Min
T_{CECK_SHFREG}/ T_{CKCE_SHFREG}	CE input to CLK	0.27/0.09	0.28/0.09	0.33/0.09	0.42/0.10	ns, Min
T_{DS_SHFREG}/ T_{DH_SHFREG}	A – D inputs to CLK	0.28/0.26	0.28/0.26	0.33/0.30	0.41/0.36	ns, Min
Clock CLK						
T_{MPW_SHFREG}	Minimum pulse width	0.55	0.65	0.78	0.91	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.

Block RAM and FIFO Switching Characteristics

Table 31: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$[1]	Clock CLK to DOUT output (without output register)[2][3]	1.57	1.80	2.08	2.44	ns, Max
	Clock CLK to DOUT output (with output register)[4][5]	0.54	0.63	0.75	0.86	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register)[2][3]	2.35	2.58	3.26	4.49	ns, Max
	Clock CLK to DOUT output with ECC (with output register)[4][5]	0.62	0.69	0.80	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with Cascade (without output register)[2]	2.21	2.45	2.80	3.19	ns, Max
	Clock CLK to DOUT output with Cascade (with output register)[4]	0.98	1.08	1.24	1.32	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs[6]	0.65	0.74	0.89	0.97	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs[7]	0.79	0.87	0.98	1.10	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode	0.66	0.72	0.80	0.93	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register)	2.17	2.38	3.01	4.15	ns, Max
	Clock CLK to BITERR (with output register)	0.57	0.65	0.76	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register)	0.64	0.74	0.90	0.98	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.71	0.79	0.92	1.10	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{RCCK\_ADDRA}/T_{RCKC\_ADDRA}$	ADDR inputs[8]	0.38/0.27	0.42/0.28	0.48/0.31	0.65/0.38	ns, Min
$T_{RDCK\_DI\_WF\_NC}/T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode[9]	0.49/0.51	0.55/0.53	0.63/0.57	0.78/0.64	ns, Min
$T_{RDCK\_DI\_RF}/T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode[9]	0.17/0.25	0.19/0.29	0.21/0.35	0.25/0.32	ns, Min
$T_{RDCK\_DI\_ECC}/T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode[9]	0.42/0.37	0.47/0.39	0.53/0.43	0.66/0.46	ns, Min
$T_{RDCK\_DI\_ECCW}/T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only[9]	0.79/0.37	0.87/0.39	0.99/0.43	1.17/0.41	ns, Min
$T_{RDCK\_DI\_ECC\_FIFO}/T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode[9]	0.89/0.47	0.98/0.50	1.12/0.54	1.32/0.65	ns, Min
$T_{RCCK\_INJECTBITERR}/T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode	0.49/0.30	0.55/0.31	0.63/0.34	0.78/0.41	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM Enable (EN) input	0.30/0.17	0.33/0.18	0.38/0.20	0.48/0.22	ns, Min
$T_{RCCK\_REGCE}/T_{RCKC\_REGCE}$	CE input of output register	0.21/0.13	0.25/0.13	0.31/0.14	0.34/0.16	ns, Min
$T_{RCCK\_RSTREG}/T_{RCKC\_RSTREG}$	Synchronous RSTREG input	0.25/0.06	0.27/0.06	0.29/0.06	0.35/0.06	ns, Min

Table 31: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{RCCK\_RSTRAM}/T_{RCKC\_RSTRAM}$	Synchronous RSTRAM input	0.27/0.35	0.29/0.37	0.31/0.39	0.34/0.40	ns, Min
$T_{RCCK\_WEA}/T_{RCKC\_WEA}$	Write Enable (WE) input (Block RAM only)	0.38/0.15	0.41/0.16	0.46/0.17	0.54/0.19	ns, Min
$T_{RCCK\_WREN}/T_{RCKC\_WREN}$	WREN FIFO inputs	0.39/0.25	0.39/0.30	0.40/0.37	0.65/0.37	ns, Min
$T_{RCCK\_RDEN}/T_{RCKC\_RDEN}$	RDEN FIFO inputs	0.36/0.26	0.36/0.30	0.37/0.37	0.60/0.38	ns, Min
Reset Delays						
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers(10)	0.76	0.83	0.93	1.06	ns, Max
$T_{RREC\_RST}/T_{RREM\_RST}$	FIFO reset recovery and removal timing(11)	1.59/–0.68	1.76/–0.68	2.01/–0.68	2.07/–0.60	ns, Max
Maximum Frequency						
$F_{MAX\_BRAM\_WF\_NC}$	Block RAM (Write first and No change modes) When not in SDP RF mode	601.32	543.77	458.09	372.44	MHz
$F_{MAX\_BRAM\_RF\_PERFORMANCE}$	Block RAM (Read first, Performance mode) When in SDP RF mode but no address overlap between port A and port B	601.32	543.77	458.09	372.44	MHz
$F_{MAX\_BRAM\_RF\_DELAYED\_WRITE}$	Block RAM (Read first, Delayed_write mode) When in SDP RF mode and there is possibility of overlap between port A and port B addresses	528.26	477.33	400.80	317.36	MHz
$F_{MAX\_CAS\_WF\_NC}$	Block RAM Cascade (Write first, No change mode) When cascade but not in RF mode	551.27	493.83	408.00	322.48	MHz
$F_{MAX\_CAS\_RF\_PERFORMANCE}$	Block RAM Cascade (Read first, Performance mode) When in cascade with RF mode and no possibility of address overlap/one port is disabled	551.27	493.83	408.00	322.48	MHz
$F_{MAX\_CAS\_RF\_DELAYED\_WRITE}$	When in cascade RF mode and there is a possibility of address overlap between port A and port B	478.27	427.35	350.88	267.38	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC	601.32	543.77	458.09	372.44	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration	484.26	430.85	351.12	254.13	MHz

Notes:

1. TRACE will report all of these parameters as T_{RCKO_DO}.
2. T_{RCKO_DOR} includes T_{RCKO_DOW}, T_{RCKO_DOPR}, and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
3. These parameters also apply to synchronous FIFO with DO_REG = 0.
4. T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
5. These parameters also apply to multirate (asynchronous) and synchronous FIFO with DO_REG = 1.
6. T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY}, T_{RCKO_AFULL}, T_{RCKO_EMPTY}, T_{RCKO_FULL}, T_{RCKO_RDERR}, T_{RCKO_WRERR}.
7. $T_{RCKO\_POINTERS}$ includes both $T_{RCKO\_RDCOUNT}$ and $T_{RCKO\_WRCOUNT}$.
8. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
9. These parameters include both A and B inputs as well as the parity inputs of A and B.
10. T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
11. RDEN and WREN must be held Low prior to and during reset. The FIFO reset must be asserted for at least five positive clock edges of the slowest clock (WRCLK or RDCLK).

Clock Buffers and Networks

Table 33: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{BCCCK\_CE}/T_{BCCKC\_CE}$(1)	CE pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O	0.08	0.10	0.12	0.10	ns
Maximum Frequency						
F_{MAX_BUFG}	Global clock tree (BUFG)	741.00	710.00	625.00	560.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 34: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BIOCKO_O}	Clock to out delay from I to O	1.04	1.14	1.32	1.48	ns
Maximum Frequency						
F_{MAX_BUFIO}	I/O clock tree (BUFIO)	800.00	800.00	710.00	710.00	MHz

Table 35: **Regional Clock Buffer Switching Characteristics (BUFR)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BRCKO_O}	Clock to out delay from I to O	0.60	0.65	0.77	1.06	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set	0.30	0.32	0.38	0.57	ns
T_{BRDO_O}	Propagation delay from CLR to O	0.71	0.75	0.96	0.93	ns
Maximum Frequency						
F_{MAX_BUFR}(1)	Regional clock tree (BUFR)	600.00	540.00	450.00	450.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

MMCM Switching Characteristics

Table 38: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$MMCM\_F_{INMAX}$	Maximum Input Clock Frequency	1066.00	933.00	800.00	800.00	MHz
$MMCM\_F_{INMIN}$	Minimum Input Clock Frequency	10.00	10.00	10.00	10.00	MHz
$MMCM\_F_{INJITTER}$	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
$MMCM\_F_{INDUTY}$	Allowable Input Duty Cycle: 10—49 MHz	25.00	25.00	25.00	25.00	%
	Allowable Input Duty Cycle: 50—199 MHz	30.00	30.00	30.00	30.00	%
	Allowable Input Duty Cycle: 200—399 MHz	35.00	35.00	35.00	35.00	%
	Allowable Input Duty Cycle: 400—499 MHz	40.00	40.00	40.00	40.00	%
	Allowable Input Duty Cycle: >500 MHz	45.00	45.00	45.00	45.00	%
$MMCM\_F_{MIN\_PSCLK}$	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum Dynamic Phase Shift Clock Frequency	550.00	500.00	450.00	450.00	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO Frequency	600.00	600.00	600.00	600.00	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO Frequency	1600.00	1440.00	1200.00	1200.00	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM Bandwidth at Typical(1)	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical(1)	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static Phase Offset of the MMCM Outputs(2)	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM Output Jitter	Note 3				
$MMCM\_T_{OUTDUTY}$	MMCM Output Clock Duty Cycle Precision(4)	0.20	0.20	0.20	0.25	ns
$MMCM\_T_{LOCKMAX}$	MMCM Maximum Lock Time	100.00	100.00	100.00	100.00	µs
$MMCM\_F_{OUTMAX}$	MMCM Maximum Output Frequency	1066.00	933.00	800.00	800.00	MHz
$MMCM\_F_{OUTMIN}$	MMCM Minimum Output Frequency(5)(6)	4.69	4.69	4.69	4.69	MHz
$MMCM\_T_{EXTFDVAR}$	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				
$MMCM\_RST_{MINPULSE}$	Minimum Reset Pulse Width	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	550.00	500.00	450.00	450.00	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300.00	300.00	300.00	300.00	MHz
$MMCM\_F_{PFDMIN}$	Minimum Frequency at the Phase Frequency Detector	10.00	10.00	10.00	10.00	MHz
$MMCM\_T_{FBDELAY}$	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
MMCM Switching Characteristics Setup and Hold						
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and Hold of Phase Shift Enable	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and Hold of Phase Shift Increment/Decrement	1.04/0.00	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase Shift Clock-to-Out of PSDONE	0.59	0.68	0.81	0.78	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK						
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI Setup/Hold	1.25/0.15	1.40/0.15	1.63/0.15	1.43/0.00	ns, Min

Table 58: **GTX Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$TJ_{10.3125}$	Total Jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$DJ_{10.3125}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{9.953}$	Total Jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$DJ_{9.953}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{9.8}$	Total Jitter(2)(4)	9.8 Gb/s	–	–	0.28	UI
$DJ_{9.8}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{8.0}$	Total Jitter(2)(4)	8.0 Gb/s	–	–	0.30	UI
$DJ_{8.0}$	Deterministic Jitter(2)(4)		–	–	0.15	UI
$TJ_{6.6\_QPLL}$	Total Jitter(2)(4)	6.6 Gb/s	–	–	0.28	UI
$DJ_{6.6\_QPLL}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{6.6\_CPLL}$	Total Jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$DJ_{6.6\_CPLL}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{5.0}$	Total Jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$DJ_{5.0}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$DJ_{4.25}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{3.75}$	Total Jitter(3)(4)	3.75 Gb/s	–	–	0.30	UI
$DJ_{3.75}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{3.2}$	Total Jitter(3)(4)	3.20 Gb/s(5)	–	–	0.2	UI
$DJ_{3.2}$	Deterministic Jitter(3)(4)		–	–	0.1	UI
$TJ_{3.2L}$	Total Jitter(3)(4)	3.20 Gb/s(6)	–	–	0.32	UI
$DJ_{3.2L}$	Deterministic Jitter(3)(4)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(3)(4)	2.5 Gb/s(7)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(3)(4)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(3)(4)	1.25 Gb/s(8)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(3)(4)		–	–	0.06	UI
TJ_{500}	Total Jitter(3)(4)	500 Mb/s	–	–	0.1	UI
DJ_{500}	Deterministic Jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of $1e^{-12}$.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 1.6 GHz and TXOUT_DIV = 1.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
8. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.

Table 59: **GTX Transceiver Receiver Switching Characteristics**

Symbol	Description		Min	Typ	Max	Units
F_{GTXRX}	Serial data rate	RX oversampler not enabled	0.500	–	F_{GTXMAX}	Gb/s
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data		–	10	–	ns
$RX_{OOBVDPP}$	OOB detect threshold peak-to-peak		60	–	150	mV
RX_{SST}	Receiver spread-spectrum tracking(1)	Modulated @ 33 KHz	–5000	–	0	ppm
RX_{RL}	Run length (CID)		–	–	512	UI
RX_{PPMTOL}	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$JT\_SJ_{12.5}$	Sinusoidal Jitter (QPLL)(3)	12.5 Gb/s	0.3	–	–	UI
$JT\_SJ_{11.18}$	Sinusoidal Jitter (QPLL)(3)	11.18 Gb/s	0.3	–	–	UI
$JT\_SJ_{10.32}$	Sinusoidal Jitter (QPLL)(3)	10.32 Gb/s	0.3	–	–	UI
$JT\_SJ_{9.95}$	Sinusoidal Jitter (QPLL)(3)	9.95 Gb/s	0.3	–	–	UI
$JT\_SJ_{9.8}$	Sinusoidal Jitter (QPLL)(3)	9.8 Gb/s	0.3	–	–	UI
$JT\_SJ_{8.0}$	Sinusoidal Jitter (QPLL)(3)	8.0 Gb/s	0.44	–	–	UI
$JT\_SJ_{6.6\_QPLL}$	Sinusoidal Jitter (QPLL)(3)	6.6 Gb/s	0.48	–	–	UI
$JT\_SJ_{6.6\_CPLL}$	Sinusoidal Jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$JT\_SJ_{5.0}$	Sinusoidal Jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$JT\_SJ_{4.25}$	Sinusoidal Jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.75}$	Sinusoidal Jitter (CPLL)(3)	3.75 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.2}$	Sinusoidal Jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI
$JT\_SJ_{3.2L}$	Sinusoidal Jitter (CPLL)(3)	3.2 Gb/s(5)	0.45	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter (CPLL)(3)	2.5 Gb/s(6)	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter (CPLL)(3)	1.25 Gb/s(7)	0.5	–	–	UI
JT_SJ_{500}	Sinusoidal Jitter (CPLL)(3)	500 Mb/s	0.4	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$JT\_TJSE_{3.2}$	Total Jitter with Stressed Eye(8)	3.2 Gb/s	0.70	–	–	UI
$JT\_TJSE_{6.6}$		6.6 Gb/s	0.70	–	–	UI
$JT\_SJSE_{3.2}$	Sinusoidal Jitter with Stressed Eye(8)	3.2 Gb/s	0.1	–	–	UI
$JT\_SJSE_{6.6}$		6.6 Gb/s	0.1	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of $1e^{-12}$.
3. The frequency of the injected sinusoidal jitter is 10 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 1.6 GHz and RXOUT_DIV = 1.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
8. Composite jitter with RX and LPM or DFE mode.

Table 67: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
XADC Reference[5]						
External Reference	V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
On-Chip Reference		Ground V_{REFP} pin to AGND, T_j = –40°C to 100°C	1.2375	1.25	1.2625	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for new BitGen option XADCEnhancedLinearity = ON.
3. See the ADC chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
4. See the Timing chapter in UG480: *7 Series FPGAs XADC User Guide* for a detailed description.
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted. On-chip reference variation is ±1%.

Configuration Switching Characteristics

Table 68: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Power-up Timing Characteristics						
T_{PL}[1]	Program latency	5	5	5	5	ms, Max
T_{POR}[1]	Power-on reset (50 ms ramp rate time)	10/50	10/50	10/50	10/50	ms, Min/Max
	Power-on reset (1 ms ramp rate time)	10/35	10/35	10/35	10/35	ms, Min/Max
$T_{PROGRAM}$	Program pulse width	250	250	250	250	ns, Min
CCLK Output (Master Mode)						
T_{ICCK}	Master CCLK output delay	150	150	150	150	ns, Min
T_{MCCKL}	Master CCLK clock Low time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
T_{MCCKH}	Master CCLK clock High time duty cycle	40/60	40/60	40/60	40/60	%, Min/Max
F_{MCCK}	Master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
	Master CCLK frequency for AES encrypted x16	50.00	50.00	50.00	35.00	MHz, Max
F_{MCCK_START}	Master CCLK frequency at start of configuration	3.00	3.00	3.00	3.00	MHz, Typ
$F_{MCCKTOL}$	Frequency tolerance, master mode with respect to nominal CCLK	±50	±50	±50	±50	%, Max
CCLK Input (Slave Modes)						
T_{SCCKL}	Slave CCLK clock minimum Low time	2.50	2.50	2.50	2.50	ns, Min
T_{SCCKH}	Slave CCLK clock minimum High time	2.50	2.50	2.50	2.50	ns, Min
F_{SCCK}	Slave CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
EMCCLK Input (Master Mode)						
T_{EMCCKL}	External master CCLK Low time	2.50	2.50	2.50	2.50	ns, Min
T_{EMCCKH}	External master CCLK High time	2.50	2.50	2.50	2.50	ns, Min
F_{EMCCK}	External master CCLK frequency	100.00	100.00	100.00	70.00	MHz, Max
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2)	100.00	100.00	100.00	70.00	MHz, Max

Table 68: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B Setup/Hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI Setup/Hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Master Flash Mode Programming Switching						
T_{BPICCO}(2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Master Flash Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] Setup/Hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 69 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 69: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.